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Vishay Semiconductors

# Hyperfast Rectifier, 3 A FRED Pt®

## eSMP® Series



**Top View** 

**Bottom View** 

### SlimSMAW (DO-221AD)



### **LINKS TO ADDITIONAL RESOURCES**



PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	3 A				
$V_R$	100 V, 200 V				
V <sub>F</sub> at I <sub>F</sub>	0.71 V				
I <sub>FSM</sub>	70 A				
t <sub>rr</sub> (typ.)	16 ns				
T <sub>J</sub> max.	175 °C				
Package	SlimSMAW (DO-221AD)				
Circuit configuration	Single				

#### **FEATURES**

- Low profile package
- · Ideal for automated placement
- · Low forward voltage drop, low power losses
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- COMPLIANT HALOGEN FREE

AUTOMOTIVE

- · AEC-Q101 qualified, class 2 whisker test
- Compatible to SOD-128 package case outline
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

### **DESCRIPTION / APPLICATIONS**

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial, and automotive applications.

### **MECHANICAL DATA**

Case: SlimSMAW (DO-221AD)

Molding compound meets UL 94 V-0 flammability rating

Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage VS-3EYH01HM	3 ,		100	V	
VS-3EYH02HM	V <sub>RRM</sub>		200	V	
Average rectified forward current	I <sub>F(AV)</sub> (1)	T <sub>C</sub> = 137 °C	3	Α	
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_J = 25$ °C, 10 ms sine pulse wave	70		
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C	

#### Note

<sup>(1)</sup> Mounted on infinite heatsink

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking	VS-3EYH01HM3	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	100	-	-	V
voltage	VS-3EYH02HM3		Ι <sub>R</sub> = 100 μΑ	200	-		
Forward voltage, per diode		V	I <sub>F</sub> = 3 A	-	0.86	0.95	V
		V <sub>F</sub>	I <sub>F</sub> = 3 A, T <sub>J</sub> = 150 °C	-	0.71	0.79	
Reverse leakage current, per diode		1	V <sub>R</sub> = V <sub>R</sub> rated	-	-	2	
		I <sub>R</sub>	$T_J = 150 ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	-	20	μA
Junction capacitance		C <sub>T</sub>	V <sub>R</sub> = 200 V	-	16	-	pF



# VS-3EYH01HM3, VS-3EYH02HM3

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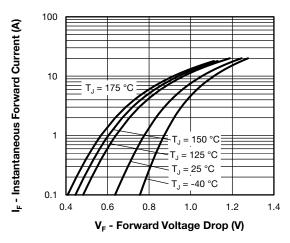
<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time		$I_F = 1.0 \text{ A}, dI_F/dt =$	= 50 A/μs, V <sub>R</sub> = 30 V	-	22	-	
		I <sub>F</sub> = 1.0 A, dI <sub>F</sub> /dt =	$I_F = 1.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		16	-	ns
	t <sub>rr</sub>	I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1A, I <sub>rr</sub> = 0.25 A		-	-	30	
		T <sub>J</sub> = 25 °C	$I_F = 3 \text{ A},$ $dI_F/dt = 200 \text{ A/}\mu\text{s},$ $V_R = 100 \text{ V}$	-	18	-	
		T <sub>J</sub> = 125 °C		-	30	-	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	2.5	-	^
		T <sub>J</sub> = 125 °C		-	4	-	A
Reverse recovery charge		T <sub>J</sub> = 25 °C		-	23	-	0
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C	1	-	60	-	nC

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C
Thermal resistance, junction to mount		R <sub>thJM</sub> <sup>(1)</sup>	Infinite heatsink	-	12	15	
Thermal resistance, junction to ambient		R <sub>thJA</sub>	Device mounted on FR4 PCB, 2 oz. standard footprint	-	120	150	°C/W
Marking dayioo	VS-3EYH01HM3		Case style SlimSMAW (DO-221AD)	3H1			
Marking device	VS-3EYH02HM3	Case Style SilffiSiviAvv (DO-221AD)		3H2			

#### Note

<sup>(1)</sup> Thermal resistance junction to mount follows JEDEC® 51-14 transient dual interface test method (TDIM)

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100 I<sub>R</sub> - Reverse Current (µA) 10 150 °C 1 125 °C 0.1 25 °C 0.01 0.001 0.0001 50 100 150 200 **V<sub>R</sub>** - Reverse Voltage (V)

Fig. 1 - Typical Forward Voltage Drop Characteristics

Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

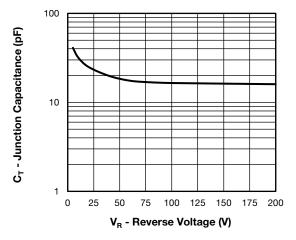


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

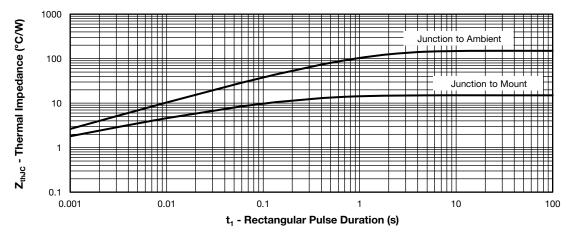


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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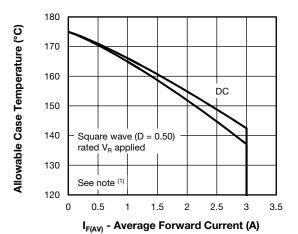


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

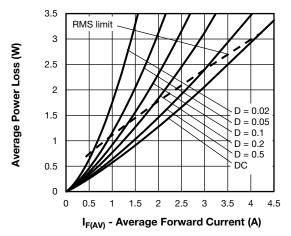


Fig. 6 - Forward Power Loss Characteristics

#### Note

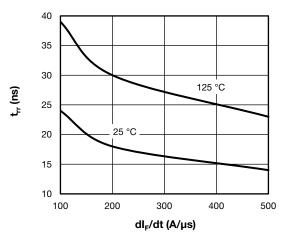


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

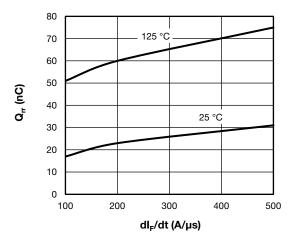


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

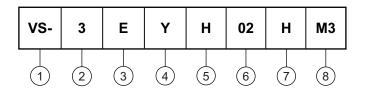
 $<sup>\</sup>begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 5)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D)}; I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$ 

## VS-3EYH01HM3, VS-3EYH02HM3

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## **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current rating (3 = 3 A)

Circuit configuration:

E = single diode

4 - Y = SlimSMAW (DO-221AD)

5 - Process type,

H = hyperfast recovery

6 - Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	PACKAGING DESCRIPTION			
VS-3EYH01HM3/H	0.033	Н	3500	7"diameter plastic tape and reel			
VS-3EYH01HM3/I	0.033	I	14 000	13"diameter plastic tape and reel			
VS-3EYH02HM3/H	0.033	Н	3500	7"diameter plastic tape and reel			
VS-3EYH02HM3/I	0.033	1	14 000	13"diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?96582</u>					
Part marking information	www.vishay.com/doc?95562				
Packaging information	www.vishay.com/doc?88869				
SPICE model	www.vishay.com/doc?96586				



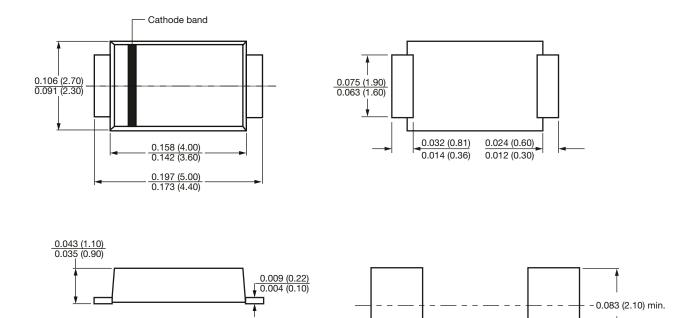
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0.055 (1.40) min.

# SlimSMAW (DO-221AD)

### **DIMENSIONS** in inches (millimeters)

### SlimSMAW (DO-221AD)



0.055 (1.40) min.

Mounting pad layout

0.118 (3.00) max.

0.228 (5.80) ref.



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